




## HEXFRED® Ultrafast Soft Recovery Diode, 80 A



SOT-227

### FEATURES

- Fast recovery time characteristic
- Electrically isolated base plate
- Large creepage distance between terminal
- Simplified mechanical designs, rapid assembly
- UL approved file E78996 
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level



RoHS  
COMPLIANT

### DESCRIPTION/APPLICATIONS

The dual diode series configuration (HFA80FA120P) is used for output rectification or freewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

PRODUCT SUMMARY	
$V_R$	1200 V
$V_F$ (typical)	2.6 V
$t_{rr}$ (typical)	25 ns
$I_{F(DC)}$ at $T_C$	40 A at 78 °C

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	$V_R$		1200	V
Continuous forward current	$I_F$	$T_C = 78\text{ °C}$	40	A
Single pulse forward current	$I_{FSM}$	$T_J = 25\text{ °C}$	400	
Maximum repetitive forward current	$I_{FRM}$	Rated $V_R$ , square wave, 20 kHz, $T_C = 60\text{ °C}$	72	
Maximum power dissipation	$P_D$	$T_C = 25\text{ °C}$	178	W
		$T_C = 100\text{ °C}$	71	
RMS isolation voltage	$V_{ISOL}$	Any terminal to case, $t = 1\text{ min}$	2500	V
Operating junction and storage temperature range	$T_J, T_{Stg}$		- 55 to 150	°C

ELECTRICAL SPECIFICATIONS ( $T_J = 25\text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	$V_{BR}$	$I_R = 100\text{ }\mu\text{A}$	1200	-	-	V	
Forward voltage	$V_{FM}$	$I_F = 25\text{ A}$	-	2.6	3.0		
		$I_F = 40\text{ A}$	See fig. 1	-	2.9		3.3
		$I_F = 80\text{ A}, T_J = 125\text{ °C}$		-	3.4	-	
Reverse leakage current	$I_{RM}$	$V_R = V_R\text{ rated}$	See fig. 2	-	2.0	$\mu\text{A}$	
		$T_J = 125\text{ °C}, V_R = 0.8 \times V_R\text{ rated}$		-	0.5	2	mA
Junction capacitance	$C_T$	$V_R = 200\text{ V}$	See fig. 3	-	43	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS ( $T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time	$t_{rr}$	$I_F = 1.0\text{ A}$ , $di_F/dt = 200\text{ A}/\mu\text{s}$ , $V_R = 30\text{ V}$	-	25	-	ns	
		$T_J = 25\text{ }^\circ\text{C}$	-	52	-		
		$T_J = 125\text{ }^\circ\text{C}$	-	110	-		
Peak recovery current	$I_{RRM}$	$I_F = 40\text{ A}$ $di_F/dt = -200\text{ A}/\mu\text{s}$ $V_R = 200\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$	-	5.9	-	A
			$T_J = 125\text{ }^\circ\text{C}$	-	10.8	-	
Reverse recovery charge	$Q_{rr}$	$T_J = 25\text{ }^\circ\text{C}$	$T_J = 25\text{ }^\circ\text{C}$	-	160	-	nC
			$T_J = 125\text{ }^\circ\text{C}$	-	630	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	$R_{thJC}$		-	-	0.7	$^\circ\text{C}/\text{W}$
Junction to case, both legs conducting			-	-	0.35	
Case to heatsink	$R_{thCS}$	Flat, greased and surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			-	1.3	-	Nm



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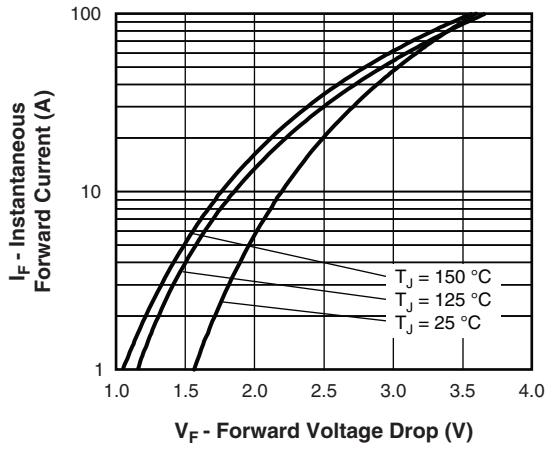


Fig. 1 - Typical Forward Voltage Drop Characteristics

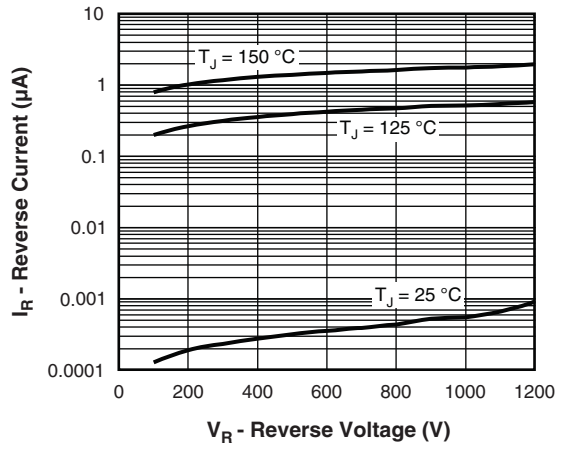


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

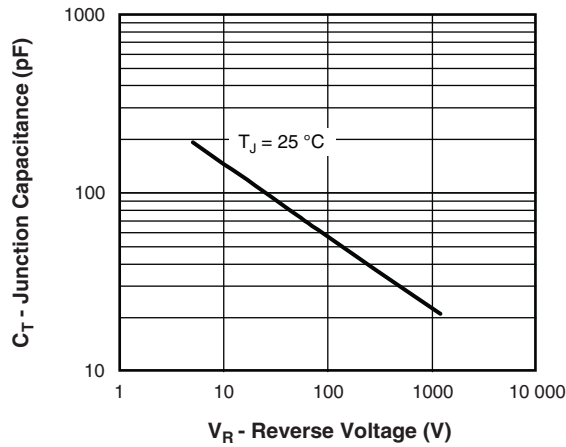


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

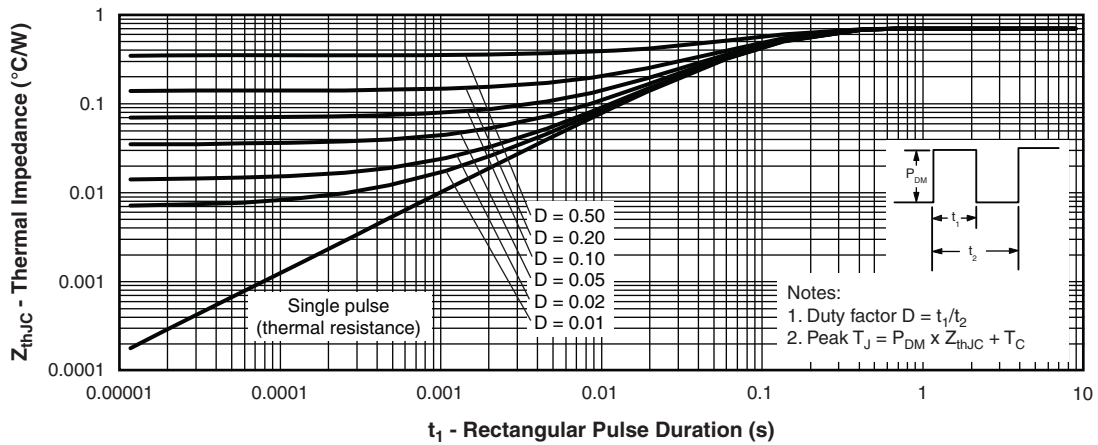


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

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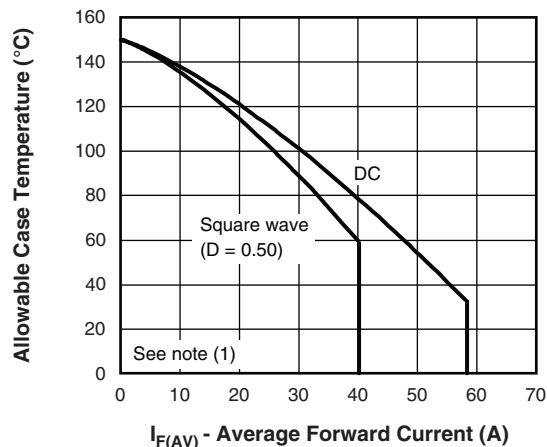


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

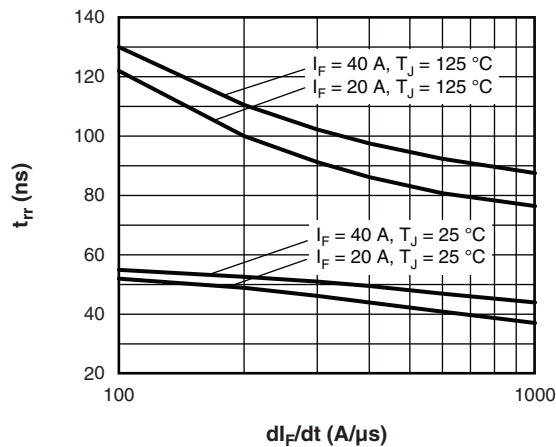


Fig. 7 - Typical Reverse Recovery Time vs.  $dI_F/dt$

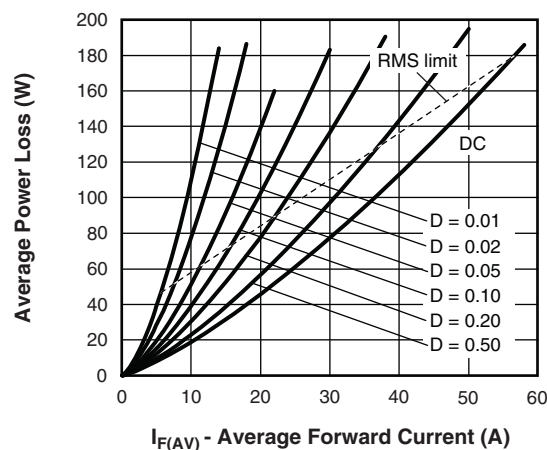


Fig. 6 - Forward Power Loss Characteristics

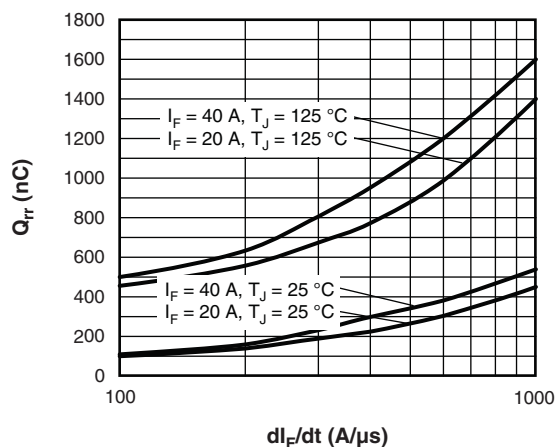


Fig. 8 - Typical Stored Charge vs.  $dI_F/dt$

**Note**

- (1) Formula used:  $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$ ;  
 $P_d$  = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6);  
 $P_{d_{REV}}$  = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = Rated  $V_R$



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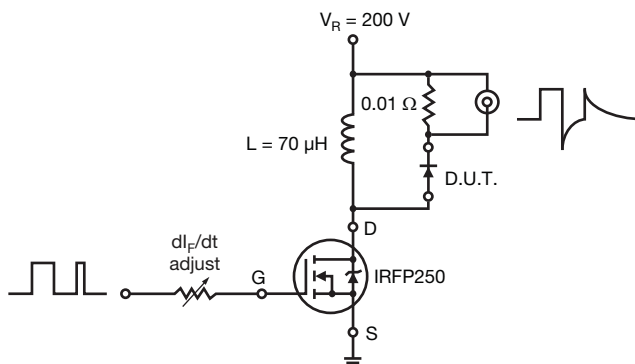
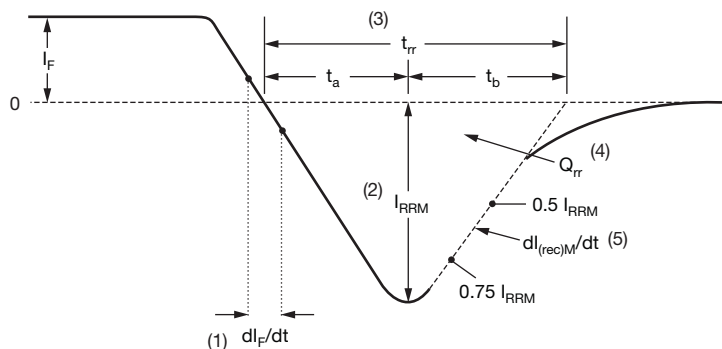


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1)  $di_F/dt$  - rate of change of current through zero crossing
- (2)  $I_{RRM}$  - peak reverse recovery current
- (3)  $t_{rr}$  - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.50 I_{RRM}$  extrapolated to zero current.
- (4)  $Q_{rr}$  - area under curve defined by  $t_{rr}$  and  $I_{RRM}$
- (5)  $dl_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

Fig. 10 - Reverse Recovery Waveform and Definitions

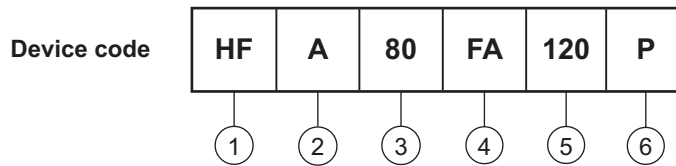
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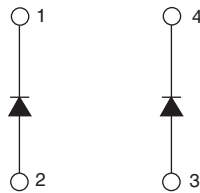
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## ORDERING INFORMATION TABLE



- 1** - HEXFRED® family
- 2** - Process designator (A = Electron irradiated)
- 3** - Average current (80 = 80 A)
- 4** - Package outline (FA = SOT-227)
- 5** - Voltage rating (120 = 1200 V)
- 6** - P = Lead (Pb)-free

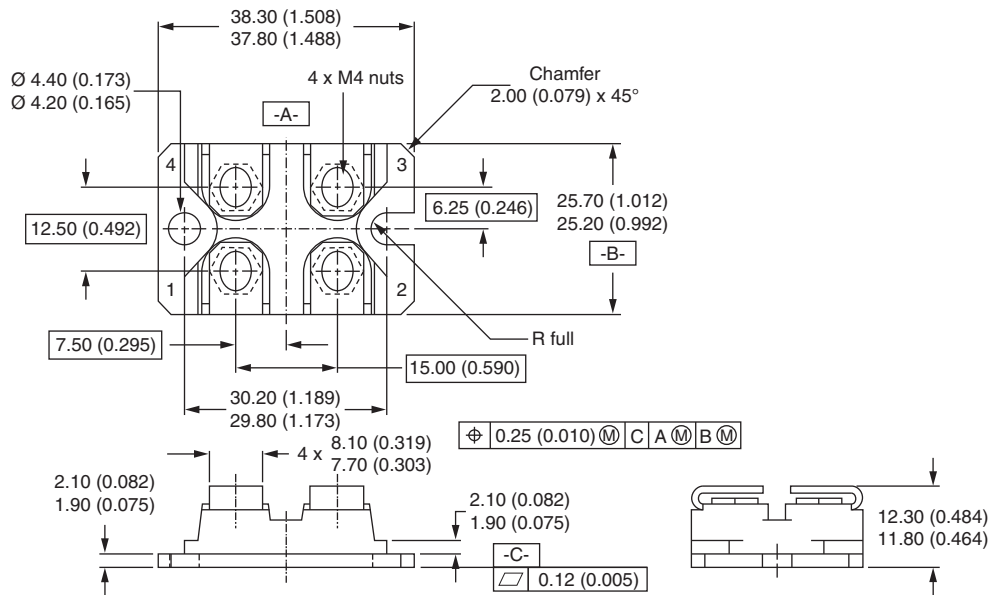
## CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95036">www.vishay.com/doc?95036</a>
Packaging information	<a href="http://www.vishay.com/doc?95037">www.vishay.com/doc?95037</a>

## SOT-227

**DIMENSIONS** in millimeters (inches)



### Notes

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter



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